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Published in:
Applied Physics Letters

Link to article, DOI:
10.1063/1.108007

Publication date:
1992

Document Version
Publisher's PDF, also known as Version of record

Link back to DTU Orbit

Citation (APA):

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Josephson oscillations and noise temperatures in YBa$_2$Cu$_3$O$_{7-x}$ grain-boundary junctions

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(Received 28 July 1992; accepted for publication 26 October 1992)

The ac Josephson effect was studied in YBa$_2$Cu$_3$O$_{7-x}$ grain-boundary junctions (GBJ) in the temperature range from 4 to 90 K. The temperature dependence of the linewidth of millimeter-wave Josephson oscillations was measured and it is shown that the derived effective noise temperatures may be as low as the physical temperature in the temperature range investigated. In the millimeter-wave range, linewidths as low as 380 MHz were found at liquid-nitrogen temperatures.

Recently, many different types of high T$_c$ superconducting weak links have been studied and some of them have shown Josephson behavior. One of the most promising types is the grain-boundary junction (GBJ) fabricated by the epitaxial growth of YBa$_2$Cu$_3$O$_{7-x}$ thin film on a bicrystal substrate. Such a GBJ is stable against thermal cycling and its parameters can be rather reproducibly controlled by changing the misorientation angle of the bicrystal substrate. Motivated by the promising applications of GBJ in dc SQUIDs, noise studies have mainly been confined to low frequencies and 1/f noise. For high-frequency applications, detailed investigations of the ac Josephson effect and wideband fluctuations in GBJ are required. This can be carried out by studying the linewidth of the Josephson radiation, as was done with weak links fabricated from conventional low T$_c$ superconductors.

To estimate the power and the spectral width of the Josephson radiation in a high T$_c$ GBJ, we consider the RSJ model to be applicable. The main parameters are the critical current $I_c$ and the normal-state resistance $R_n$. The total power $P$ of the Josephson radiation supplied to an external circuit with impedance $R$ is equal to

$$P = 2V^2 \left[ \left( V^2 + V_n^2 \right) - V \right] \sqrt{\frac{V^2}{V^2 + V_n^2}},$$

(1)

where $V_c = I_c R_n$ is the characteristic voltage of the Josephson junction. The maximum power $P_{max} = V_c^2/R_n$ is reached at $V > V_c$. For an YBCO GBJ at 77 K, $V_c$ is of the order 0.1 mV and with a typical $R_n \sim 100 \Omega$, we get $P \sim 10^{-10}$ W.

Two main sources of voltage fluctuations may be considered in GBJs, broadband thermal noise and low-frequency 1/f noise. The latter may result both from fluctuations in the critical current and from fluctuations of the normal-state resistance. For broadband thermal fluctuations, which are the dominant here, the linewidth is

$$\delta f = 4\pi \left( \frac{2e}{h} \right)^2 kT \frac{R_n}{R_D} \left[ 1 + \left( \frac{V}{V_c} \right)^2 \right],$$

(2)

where $R_D$ is the dynamic resistance. The linewidth in Eq. (2) is always larger than the minimum value $\delta f = 4\pi \left( \frac{2e}{h} \right)^2 kT R_n$, which is reached for $I > I_c$ and will be used for estimates. At liquid-nitrogen temperatures and for a GBJ with $R_n = 1 \Omega$, we get $\delta f \sim 3$ GHz.

In the present study of the Josephson linewidth, we use the same indirect technique based on the self-detected dc response of the Josephson junction to low-intensity microwave radiation, as was used in a study of low T$_c$ microcontacts. The technique is based on the analytical properties of the voltage dependence of the dc response $\Delta V(V)$, which is the voltage difference between the IV curves with and without applied microwave radiation. $\Delta V(V)$ shows an odd symmetric resonance at the voltages $V = (h/2e)f$ and the difference $\delta V$ between voltages $V_+$ and $V_-$ corresponding to the positions of the maximum and the minimum of the response $\Delta V$ in this region gives us a linewidth $\delta f = (2e/h)\delta V$. Thin-film YBa$_2$Cu$_3$O$_{7-x}$ bicrystals were prepared by depositing c-axis oriented epitaxial YBa$_2$Cu$_3$O$_{7-x}$ films on SrTiO$_3$ and Y-ZrO$_2$ bicrystals using laser ablation deposition. The thin-film bicrystal was then patterned by another laser into a number of bridges, each crossing a grain boundary and having widths ranging from 5 to 300 µm. The parameters are shown in Table I.

The sample holder had a loosely coupled 60–90 GHz waveguide connection to the sample and ~70 GHz radiation from a Gunn oscillator could be applied. A lock-in technique was used to measure the derivative of the dc IV characteristics and the dc response $\Delta F(V)$. The response measurements were obtained by an on-off modulation of the microwave power; the modulation frequency was 531 Hz, determining the minimum frequency of noise observations. The sample holder was placed inside a vacuum can immersed in a glass helium Dewar surrounded by a double µ-metal shield. All measurements were made in an rf shielded room.

The main results are based on the assumption that the RSJ model applies. Hence, we first discuss the validity of this assumption. For the GBJ used in this study, the dc IV characteristics agreed with the hyperbolic dependence predicted by the RSJ model for $R_n \sim 0.1$ to 1 Ω. For narrow and high-ohmic GBJs with $R_n > 1$ Ω, hysteresis was observed in the IV curve at low temperatures with no stable

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TABLE I. Parameters of grain-boundary junctions used for linewidth measurements.

<table>
<thead>
<tr>
<th>Junc. No.</th>
<th>Substrate</th>
<th>Misorient. angle (°)</th>
<th>Width (µm)</th>
<th>$R_n$ (Ω)</th>
<th>$I_c(4.5 \text{ K})$ (mA)</th>
<th>$V_c(4.5 \text{ K})$ (mV)</th>
</tr>
</thead>
<tbody>
<tr>
<td>GBJ11</td>
<td>SrTiO$_3$</td>
<td>25°</td>
<td>5</td>
<td>4.6</td>
<td>0.4</td>
<td>1.8</td>
</tr>
<tr>
<td>GBJ12</td>
<td>SrTiO$_3$</td>
<td>25°</td>
<td>16</td>
<td>0.57</td>
<td>2.0</td>
<td>1.1</td>
</tr>
<tr>
<td>GBJ13</td>
<td>SrTiO$_3$</td>
<td>25°</td>
<td>88</td>
<td>0.07</td>
<td>7.0</td>
<td>0.5</td>
</tr>
<tr>
<td>GBJ21</td>
<td>Y-ZrO$_2$</td>
<td>45°</td>
<td>34</td>
<td>0.67</td>
<td>0.11</td>
<td>0.07</td>
</tr>
<tr>
<td>GBJ22</td>
<td>Y-ZrO$_2$</td>
<td>45°</td>
<td>93</td>
<td>0.22</td>
<td>0.35</td>
<td>0.08</td>
</tr>
</tbody>
</table>

Bias point at voltages from zero to several hundreds $\mu$V, while for low-ohmic GBJ, there was no hysteresis in the $IV$ curves. These observations suggest the hysteresis may be due to the shunting of the Josephson oscillations by the intrinsic stray capacitance, which we estimate to be around 1 pF for a 5-µm-wide GBJ on SrTiO$_3$. The $IV$ characteristics of the wider GBJ with resistance $R_n < 0.1$ Ω are also different from that of the RSJ model. In Fig. 1, the $IV$ curve and mm-wave response $\Delta V$ versus voltage $V$ are shown for a GBJ with $R_n = 0.07$ Ω. An excess current not consistent with the RSJ model is clearly seen on the $IV$ curve at $I = I_c$. This excess current is due to flux motion along the GBJ. The deviation from the RSJ model, however, does not prevent us from measuring the response curve as in the hysteretic case. The corresponding data are shown in Fig. 1 (curve 3). The response $\Delta V$ is proportional to the differential resistance $R_D$ (curve 2) at low voltages; at voltages close to $(h/2e)f$, the response shows a resonance structure due to the interaction between the externally applied 72 GHz signal and the Josephson oscillations. The width $\delta V$ of this resonance structure, calculated as a difference in the voltages $V_+$ and $V_-$ corresponding to the minimum and the maximum response, was equal to $(0.8 \pm 0.1) \mu$V at $T = 78$ K corresponding to a Josephson linewidth $\delta f = (2e/h)\delta V = (380 \pm 50)$ MHz at liquid-nitrogen temperature. The amplitudes of the resonance response at $V = (h/2e)f$ of low-ohmic GBJ were always less than the response at low voltage (see curve 3 in Fig. 1): this means that the ac Josephson effect in low-ohmic GBJ is comparatively depressed.

Figure 2 shows the same data for GBJ12. Here, the $IV$-curve is close to being hyperbolic and the differential resistance $R_D(V)$ has a maximum at low voltages and decreases with increasing voltage approaching a constant value. The response $\Delta V$ is proportional to the differential resistance at low voltages, and at voltages around $(h/2e)f$, it shows an odd-symmetric resonance. The absence of resonances at voltages $n \cdot (h/2e)f$ shows that the response is measured at sufficiently low intensity and the absence of $(1/n)(h/2e)f$ resonances demonstrates a pure sin $\varphi$ current-phase relationship.

In order to get quantitative results, we calculated the normalized response $h(V) = (\Delta V/R_D) I/V$ in the RSJ model with thermal fluctuations and compared it to the normalized response calculated from experimental data shown in Fig. 2. The comparison is shown in the inset. Two fitting parameters were used—the amplitude of the rf current induced in the GBJ by external radiation and the linewidth $\delta f$ of the Josephson radiation. As it can be seen from Fig. 2, the fit is good within an accuracy of a few percent. This confirms that the response of the GBJ can be described in terms of the RSJ model with thermal fluctuation. Other results of the RSJ model can therefore be considered applicable to GBJ and we will use Eq. (3) to determine the effective temperature $T_N$ from the experimental values of linewidth $\delta f$. 

FIG. 1. (1) dc $IV$-characteristic, (2) voltage dependence of the differential resistance, $R_D(V)$, and (3) response $\Delta V(V)$ to 73 GHz radiation for $YBa_2Cu_3O_{7-x}$ grain-boundary junction GBJ13. The temperature is $T = 78$ K.

FIG. 2. (1) dc $IV$ characteristic, (2) differential resistance, and (3) response to 72 GHz radiation for $YBa_2Cu_3O_{7-x}$ grain-boundary junction GBJ12 at $T = 78$ K. The inset shows the normalized response $h(V) = (\Delta V/R_D) I/V$, calculated and experimental.
In Fig. 3 we present the noise temperatures $T_N$ for three GBJs as a function of the physical temperature $T$ in the range from 4.5 to 90 K. The general trend is that, in this wide temperature range, the noise temperature follows the physical temperature. The best agreement between $T_N$ and $T$ is obtained for GBJs having small characteristic voltages $V_c(T) < (\hbar/2e)f$ (filled squares and triangles). A larger difference between $T_N$ and $T$ was observed for GBJ12 with $V_c(T) > (\hbar/2e)f$ (unfilled squares) at intermediate temperatures. For some junctions of the microbridge type, a fit was not possible, indicating nonthermal noise sources dominating.

The data presented in Fig. 3 shows that wideband thermal noise is the dominant cause of the observed Josephson linewidth. This is especially so for Josephson oscillations at voltages $(\hbar/2e)f > V_c$. In this case, the bias current $I$ is much larger than critical current $I_c$ so that low frequency fluctuations of the critical current will not contribute to voltage fluctuations. The $1/f$ noise from resistance fluctuations can also give such a contribution, but as it is seen from the data, this is not the case here.

The largest difference between $T$ and $T_N$ was observed for $(\hbar/2e)f < V_c$ and in the range of intermediate temperatures. We suspect $1/f$ noise due to critical current fluctuations to be responsible for this extra contribution to the linewidth because, in this case, current bias is closer to $I_c^*$. The abrupt changes in the $T_N(T)$ dependence in the intermediate temperature range correspond to the spontaneous changes in $I_c(T)$ and this also indicates a contribution from the critical current fluctuations. The GBJ had a highly inhomogeneous spatial distribution of the critical current density, as was seen from the $I_c(H)$ dependence, and hence, the GBJ may be considered more as a multi-junction interferometer. Magnetic flux can come and go in the loops of this interferometer giving rise to changes in the critical current of the GBJ and to noise fluctuations. Like other interferometers, the GBJ should have a maximum responsivity $\delta I_c/\delta B$ when $LI_c - \Phi_0$, and this may be the cause of the extra noise as observed at some temperatures.

The authors are grateful to E. A. Stepantsov for supplying the bicrystal Y-ZrO$_2$ substrates, to P. M. Shadrin for the laser probe measurements of the inhomogeneity of the samples, and to J. Lacey and A. Gupta for help with the substrate and film fabrication. This work was partly funded under the Danish Technical Research Council (STVF) HTSC program.